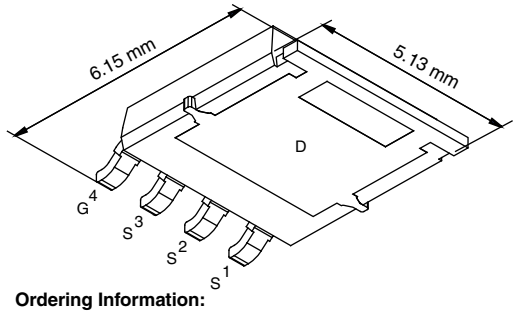
N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
80	0.0080 at V_{GS} = 10 V	60[a]	17.1 nC
	0.0088 at V_{GS} = 6.0 V	60[a]	
	0.0115 at V_{GS} = 4.5 V	54	

PowerPAK® SO-8L Single



Ordering Information:
SiJ478DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

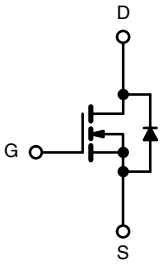
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Primary Side Switching
- Synchronous Rectification
- DC/AC Inverters
- LED Backlighting



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	60[a]	A
	T_C = 70 °C		52.7	
	T_A = 25 °C		18.6[b, c]	
	T_A = 70 °C		14.9[b, c]	
Pulsed Drain Current (t = 100 µs)		I_{DM}	150	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	60a	
	T_A = 25 °C		4.5[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	30	
Single Pulse Avalanche Energy		E_{AS}	45	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	62.5	W
	T_C = 70 °C		40	
	T_A = 25 °C		5[b, c]	
	T_A = 70 °C		3.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[d, e]			260	

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, f]	t ≤ 10 s	R_{thJA}	20	25	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.5	2.0	

Notes

a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions is 70 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	80			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		37		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.1		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.4		2.6	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0064	0.0080	Ω
		V_{GS} = 6 V, I_D = 15 A		0.0070	0.0088	
		V_{GS} = 4.5 V, I_D = 10 A		0.0087	0.0115	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 20 A		60		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz		1855		pF
Output Capacitance	C_{oss}			950		
Reverse Transfer Capacitance	C_{rss}			76		
Total Gate Charge	Q_g	V_{DS} = 40 V,V_{GS} = 10 V, I_D = 10 A		35.5	54	nC
		V_{DS} = 40 V, V_{GS} = 6 V, I_D = 10 A		22	33	
		V_{DS} = 40 V,V_{GS} = 4.5 V, I_D = 10 A		17.1	26	
Gate-Source Charge	Q_{gs}			5.3		
Gate-Drain Charge	Q_{gd}			7.3		
Output Charge	Q_{oss}	V_{DS} = 40 V, V_{GS} = 0 V		57	86	
Gate Resistance	R_g	f = 1 MHz	0.5	1.3	2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 4 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		12	24	ns
Rise Time	t_r			8	16	
Turn-Off DelayTime	$t_{d(off)}$			32	64	
Fall Time	t_f			7	14	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 4 Ω $I_D \cong$ 10 A, V_{GEN} = 6.0 V, R_g = 1 Ω		14	28	
Rise Time	t_r			11	22	
Turn-Off DelayTime	$t_{d(off)}$			30	60	
Fall Time	t_f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			60	A
Pulse Diode Forward Current (t = 100 µs)	I_{SM}				150	
Body Diode Voltage	V_{SD}	I_S = 5 A		0.76	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/µs, T_J = 25 °C		38	75	ns
Body Diode Reverse Recovery Charge	Q_{rr}			36	70	nC
Reverse Recovery Fall Time	t_a			19		ns
Reverse Recovery Rise Time	t_b			19		

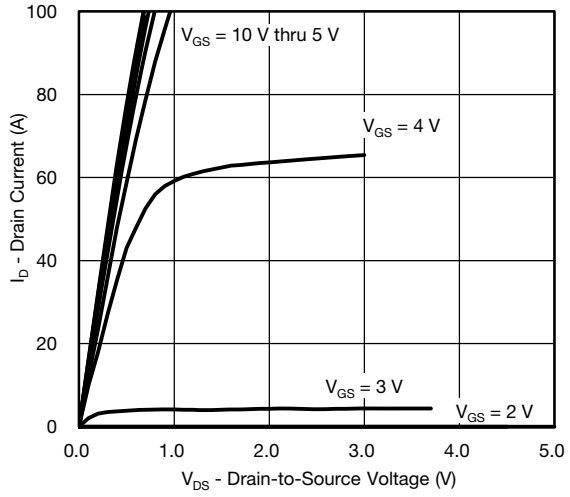
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

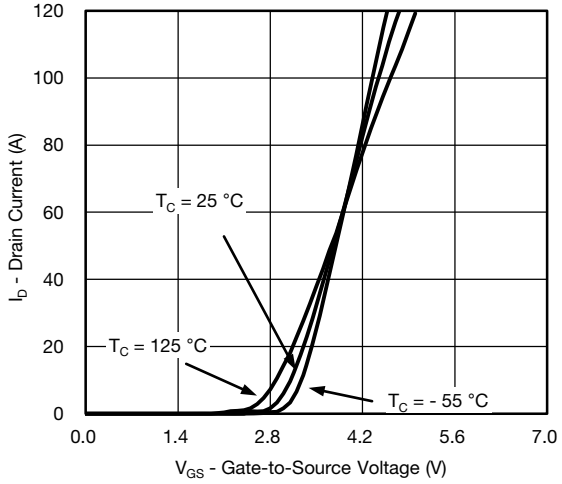
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

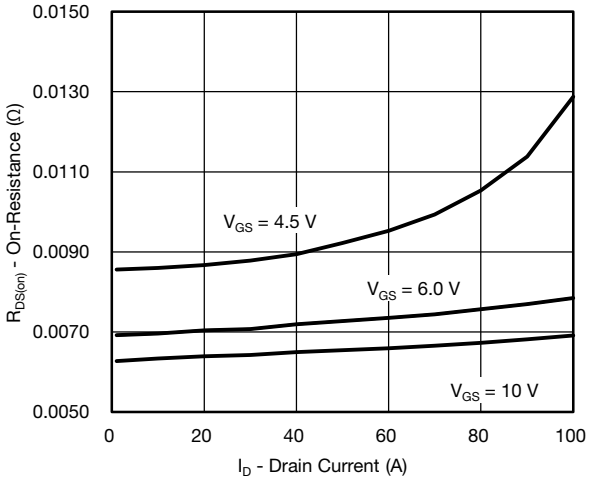
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



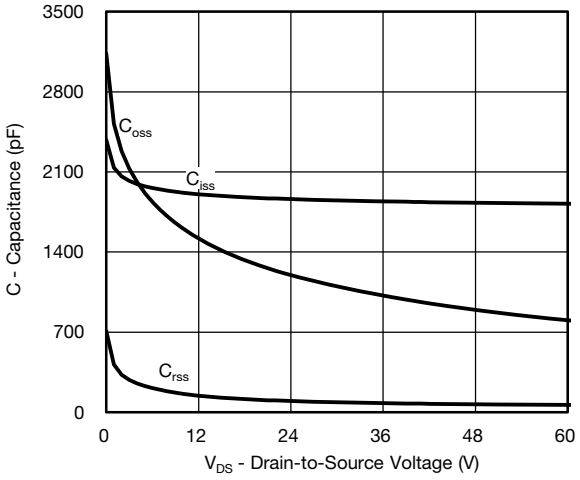
Output Characteristics



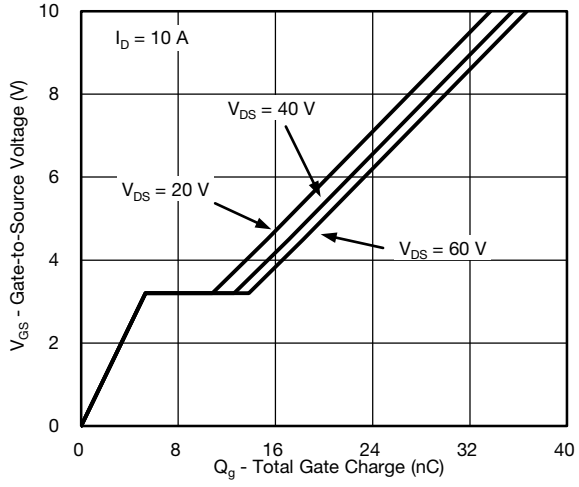
Transfer Characteristics



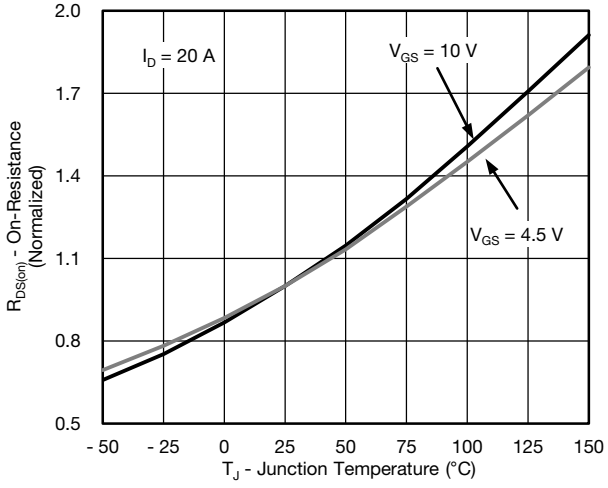
On-Resistance vs. Drain Current



Capacitance

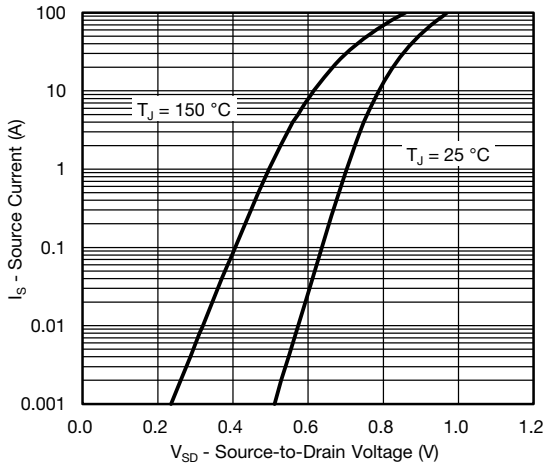


Gate Charge

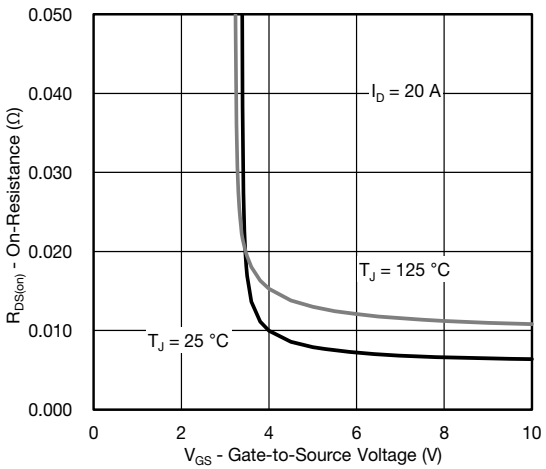


On-Resistance vs. Junction Temperature

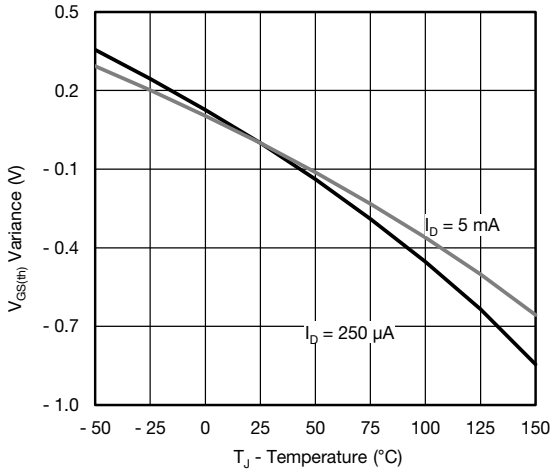
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



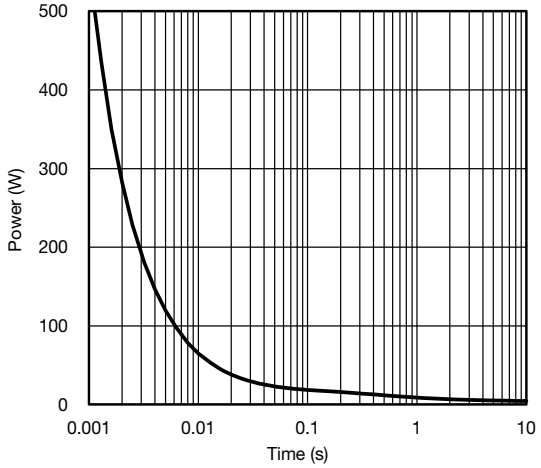
Source-Drain Diode Forward Voltage



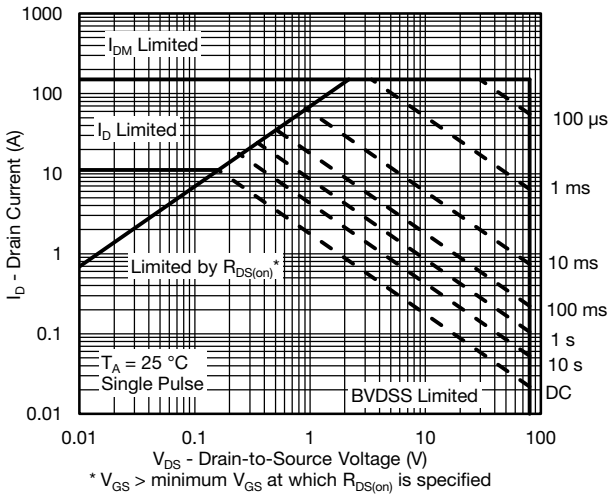
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

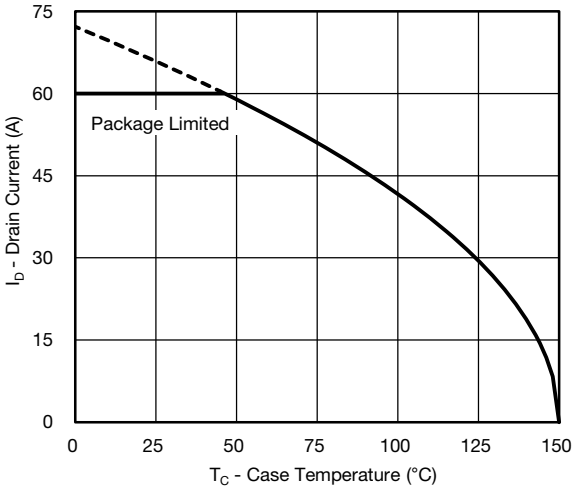


Single Pulse Power, Junction-to-Ambient

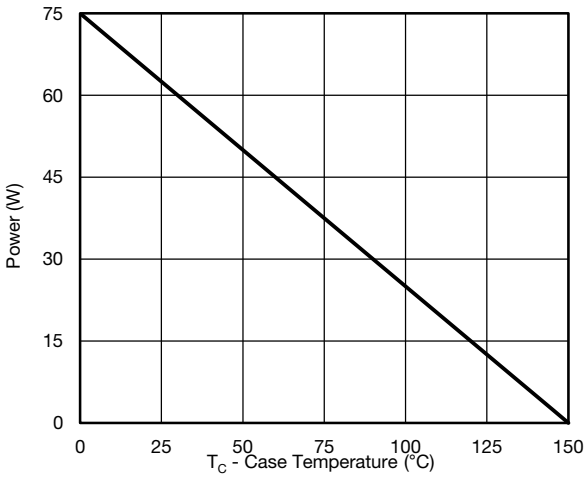


Safe Operating Area, Junction-to-Ambient

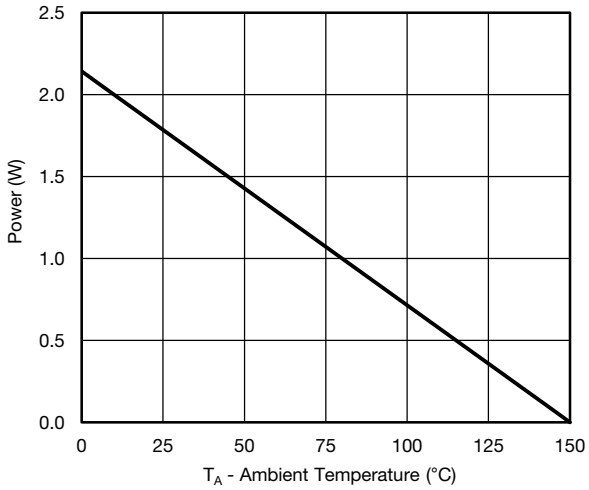
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



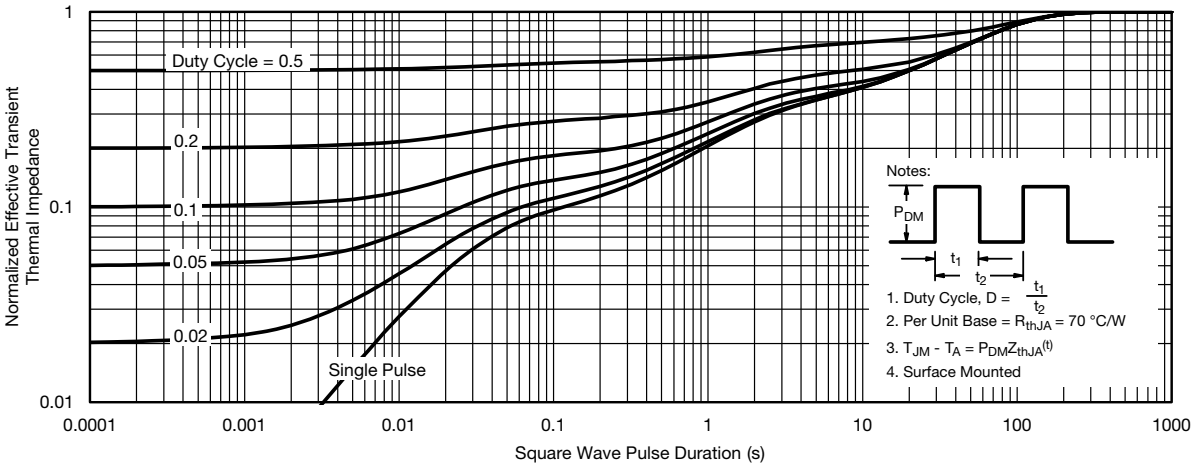
Power, Junction-to-Case



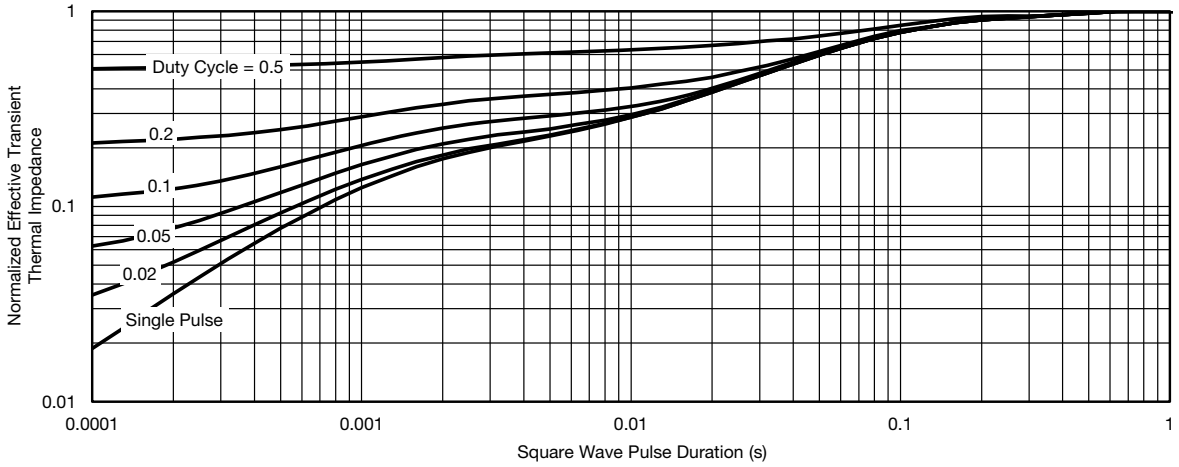
Power, Junction-to-Ambient

** The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.*

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



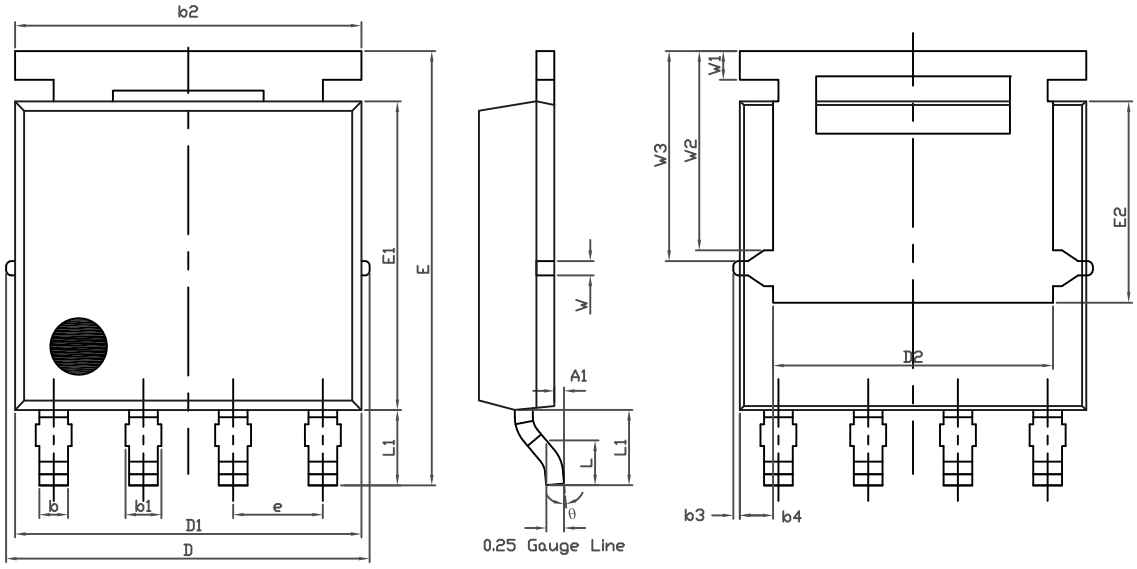
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

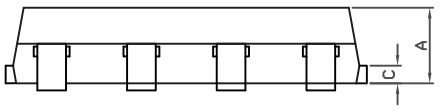
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62868.

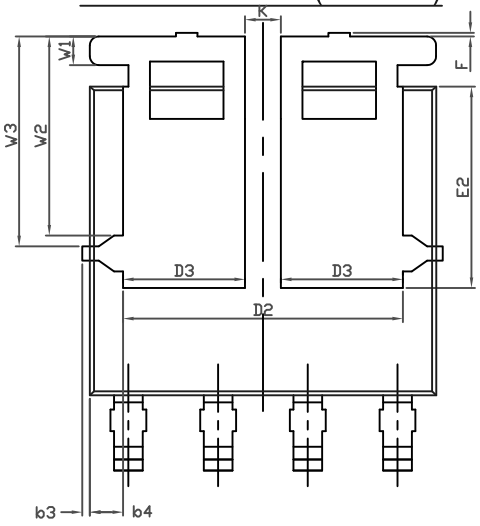
PowerPAK® SO-8L Case Outline for Non-Al Parts



TOPSIDE VIEW

BACKSIDE VIEW(SINGLE)





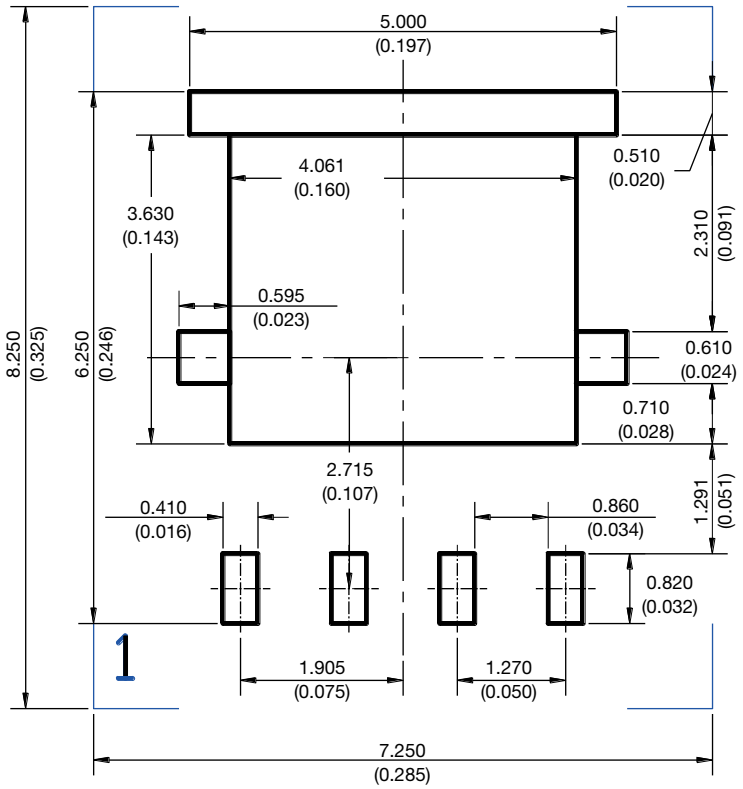
BACKSIDE VIEW(DUAL)

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
q	0°	-	10°	0°	-	10°
ECN: C15-1122-Rev. C, 07-Sep-15 DWG: 5976						

Note

- Millimeters will gover

RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)

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